## HRF32

## Silicon Schottky Barrier Diode for Rectifying

# **HITACHI**

ADE-208-164D(Z) Rev 4 Jul. 1997

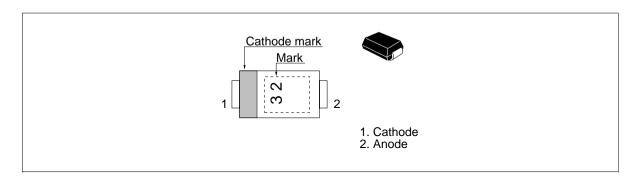
#### **Features**

- Good for high-frequency rectify.
- LRP structure ensures higher reliability.

### **Ordering Information**

Type No.	Laser Mark	Package Code
HRF32	32	LRP

#### **Outline**





### HRF32

### **Absolute Maximum Ratings (Ta = 25^{\circ}C)**

Item	Symbol	Value	Unit
Repetitive peak reverse voltage	V <sub>RRM</sub> *1	90	V
Average rectified current	I <sub>o</sub> *1	1.0	A
Non-Repetitive peak forward surge current	I <sub>FSM</sub> *2	20	A
Junction temperature	Tj	125	°C
Storage temperature	Tstg	-40 to +125	°C

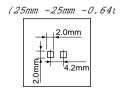
Note: 1. See from Fig.4 to Fig.7

Note: 2. 10msec half sine wave 1 pulse

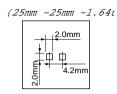
#### **Electrical Characteristics (Ta = 25^{\circ}C)**

Item	Symbol	Min	Тур	Max	Unit	Test Condition
Forward voltage	V <sub>F</sub>	_	_	0.8	V	I <sub>F</sub> = 1.0A
Reverse current	I <sub>R</sub>	_	_	1.0	mA	V <sub>R</sub> = 90V
ESD-Capability	_	150	_	_	V	C=200pF , R=0 $\Omega$ , Both forward and reverse direction 1 pulse.
Thermal resistance	Rth(j-a)	_	_	108	°C/W	Alumina board *1
		_	_	157		Print board *2

Note: 1. Alumina board



Note: 2. Print board



#### **Main Characteristic**

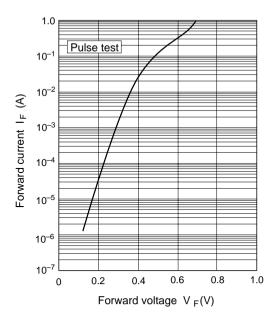


Fig.1 Forward current Vs. Forward voltage

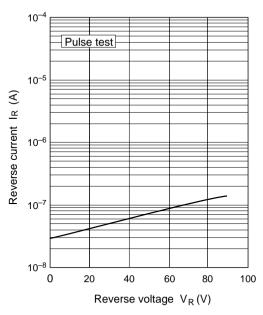


Fig.2 Reverse current Vs. Reverse voltage

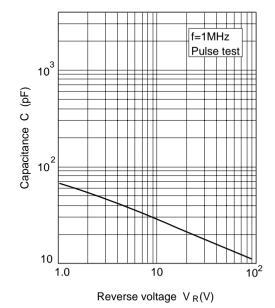


Fig.3 Capacitance Vs. Reverse voltage

#### **Main Characteristic**

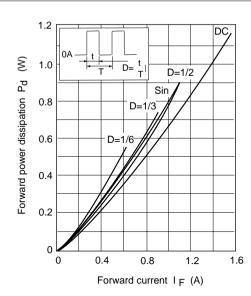


Fig.4 Forward p ower dissipation Vs. Forward current

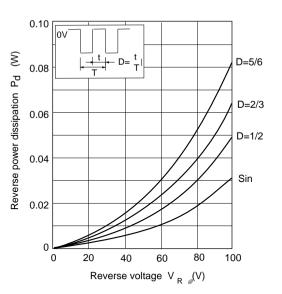


Fig.5 Reverse power dissipation Vs. Reverse voltage

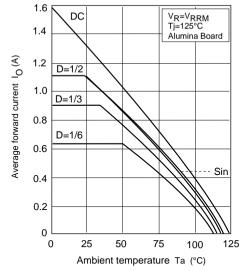


Fig.6 Average forward current Vs. Ambient temperature

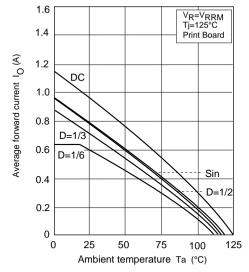
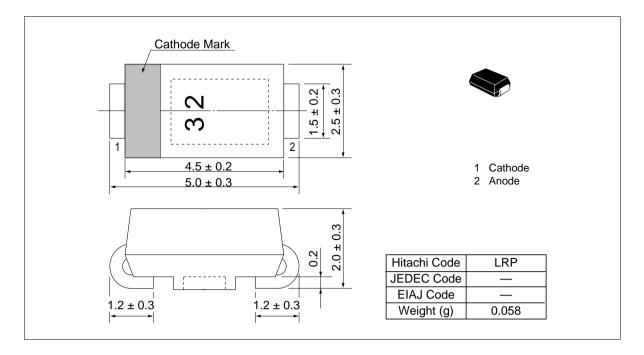


Fig.7 Average forward current Vs. Ambient temperature

### **Package Dimensions**

Unit: mm



#### **Cautions**

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